

PowerMOS transistor**BUK444-500B****GENERAL DESCRIPTION**

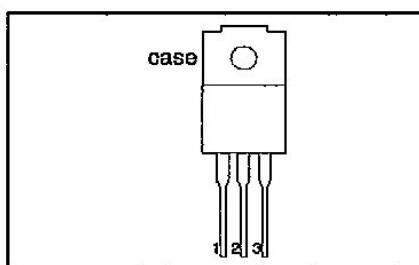
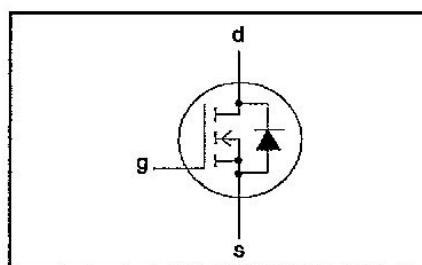
N-channel enhancement mode field-effect power transistor in a plastic full-pack envelope. The device is intended for use in Switched Mode Power Supplies (SMPS), motor control, welding, DC/DC and AC/DC converters, and in general purpose switching applications.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	500	V
I_D	Drain current (DC)	1.9	A
P_{tot}	Total power dissipation	25	W
$R_{DS(on)}$	Drain-source on-state resistance	2.8	Ω

PINNING - SOT186

PIN	DESCRIPTION
1	gate
2	drain
3	source
case	isolated

PIN CONFIGURATION**SYMBOL****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	500	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	500	V
$\pm V_{GS}$	Gate-source voltage	-	-	30	V
I_D	Drain current (DC)	$T_{hs} = 25^\circ\text{C}$	-	1.9	A
I_D	Drain current (DC)	$T_{hs} = 100^\circ\text{C}$	-	1.2	A
I_{DM}	Drain current (pulse peak value)	$T_{hs} = 25^\circ\text{C}$	-	7.6	A
P_{tot}	Total power dissipation	$T_{hs} = 25^\circ\text{C}$	-	25	W
T_{stg}	Storage temperature	-	-55	150	°C
T_J	Junction Temperature	-	-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th,j-mb}$	Thermal resistance junction to mounting base	with heatsink compound	-	-	5	K/W
$R_{th,j-a}$	Thermal resistance junction to ambient		-	55	-	K/W

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STATIC CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.25 \text{ mA}$	500	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1 \text{ mA}$	2.1	3.0	4.0	V
I_{oss}	Zero gate voltage drain current	$V_{DS} = 500 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25^\circ\text{C}$	-	2	20	μA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 500 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125^\circ\text{C}$	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 30 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nA
$R_{DS(on)}$	Drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 1.2 \text{ A}$	-	2.4	2.8	Ω

DYNAMIC CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_s	Forward transconductance	$V_{DS} = 25 \text{ V}; I_D = 1.2 \text{ A}$	1.9	2.5	-	S
C_{iss}	Input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}$	-	400	500	pF
C_{oss}	Output capacitance		-	55	80	pF
C_{rss}	Feedback capacitance		-	20	55	pF
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 30 \text{ V}; I_D = 2.3 \text{ A}; V_{GS} = 10 \text{ V}; R_{GS} = 50 \Omega; R_{gen} = 50 \Omega$	-	15	20	ns
t_r	Turn-on rise time		-	40	60	ns
$t_{d(off)}$	Turn-off delay time		-	50	65	ns
t_f	Turn-off fall time		-	30	40	ns
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

ISOLATION $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	$R.H. \leq 65\% ; \text{clean and dustfree}$	-	-	1500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1 \text{ MHz}$	-	12	-	pF

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS $T_{hs} = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	2.1	A
I_{DRM}	Pulsed reverse drain current	-	-	-	8.4	A
V_{SD}	Diode forward voltage	$I_F = 2.1 \text{ A}; V_{GS} = 0 \text{ V}$	-	1.0	1.3	V
t_r	Reverse recovery time	$I_F = 2.1 \text{ A}; -dI_F/dt = 100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_R = 100 \text{ V}$	-	270	-	ns
Q_{rr}	Reverse recovery charge		-	2.0	-	μC

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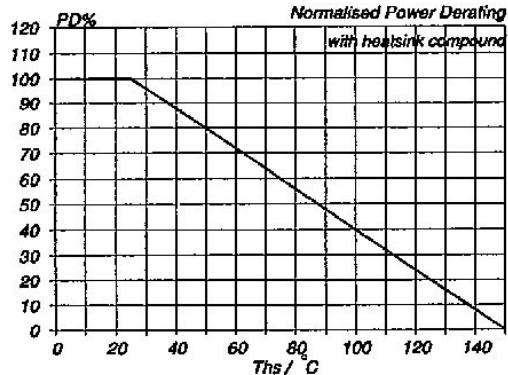


Fig. 1. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D,25^\circ C} = f(T_{hs})$

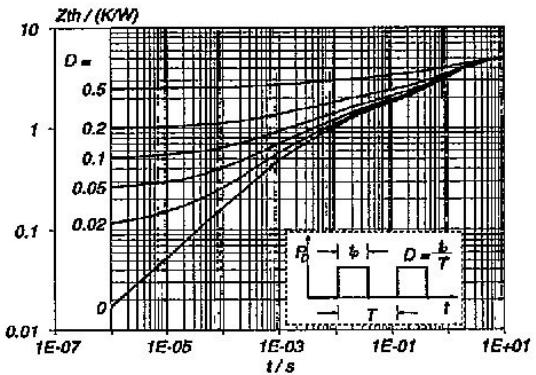


Fig. 4. Transient thermal impedance.
 $Z_{th,Hs} = f(t); \text{parameter } D = t_p/T$

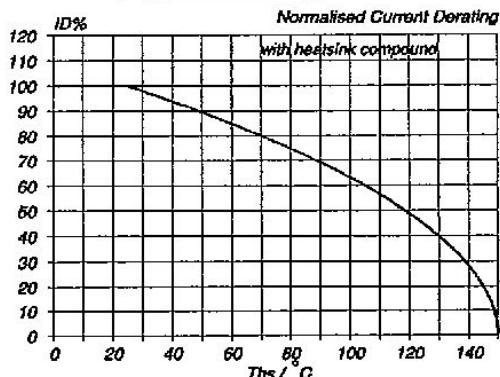


Fig. 2. Normalised continuous drain current.
 $ID\% = 100 \cdot I_D / I_{D,25^\circ C} = f(T_{hs}); \text{conditions: } V_{GS} \geq 10 \text{ V}$

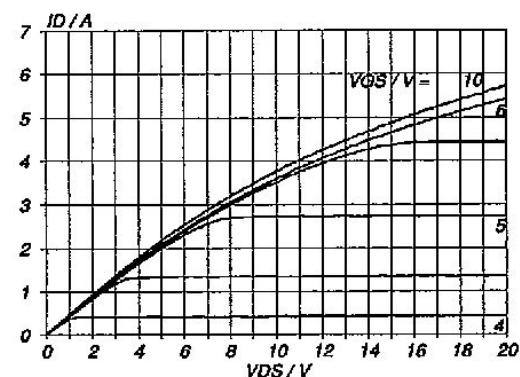


Fig. 5. Typical output characteristics, $T_J = 25^\circ C$.
 $I_D = f(V_{DS}); \text{parameter } V_{GS}$

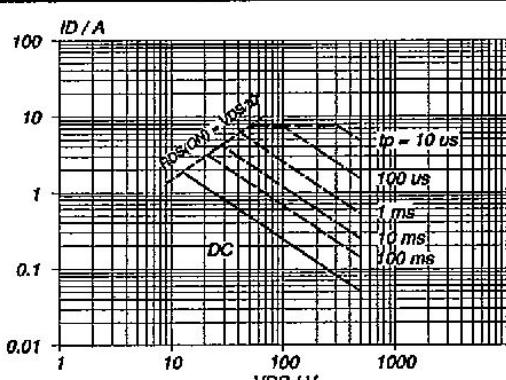


Fig. 3. Safe operating area, $T_{hs} = 25^\circ C$
 $I_D \& I_{DM} = f(V_{DS}); I_{DM} \text{ single pulse}; \text{parameter } t_p$

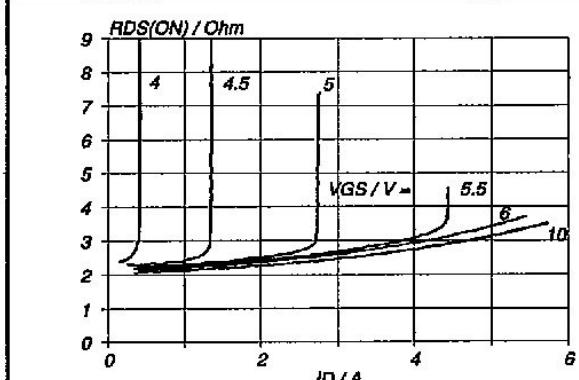


Fig. 6. Typical on-state resistance, $T_J = 25^\circ C$.
 $R_{DS(ON)} = f(I_D); \text{parameter } V_{GS}$

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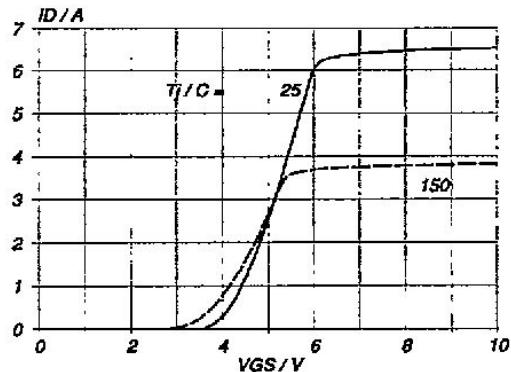


Fig.7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25 \text{ V}$; parameter T_j

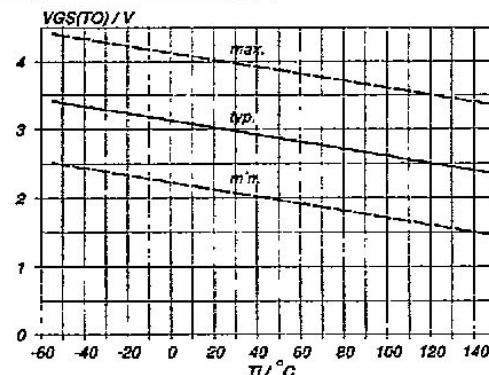


Fig.10. Gate threshold voltage.
 $V_{GS(TO)} = f(T_j)$; conditions: $I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$

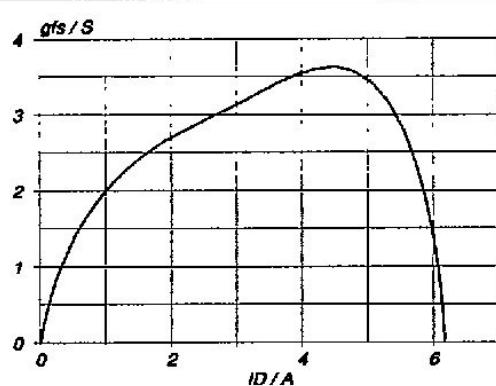


Fig.8. Typical transconductance, $T_j = 25^\circ\text{C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25 \text{ V}$

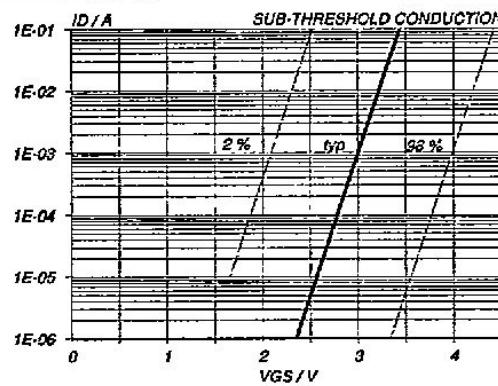


Fig.11. Sub-threshold drain current.
 $I_D = f(V_{GS})$; conditions: $T_j = 25^\circ\text{C}$; $V_{DS} = V_{GS}$

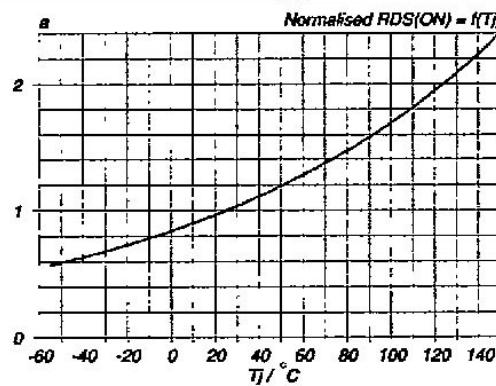


Fig.9. Normalised drain-source on-state resistance.
 $a = R_{DS(ON)}/R_{DS(ON)25^\circ\text{C}} = f(T_j)$; $I_D = 1.5 \text{ A}$; $V_{GS} = 10 \text{ V}$

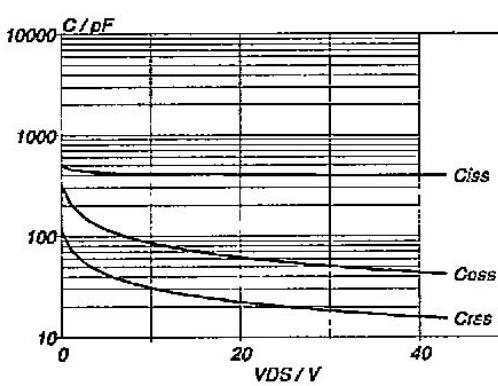


Fig.12. Typical capacitances, C_{iss} , C_{oss} , C_{rees} .
 $C = f(V_{DS})$; conditions: $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

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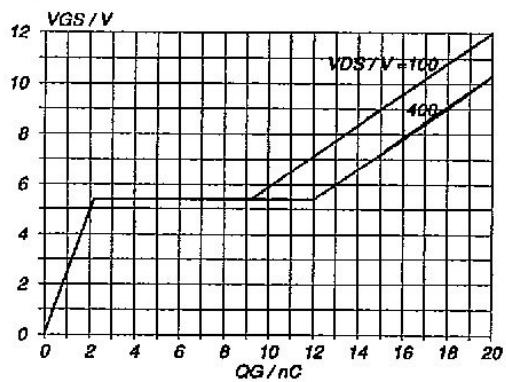


Fig.13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 3.7 \text{ A}$; parameter V_{DS}

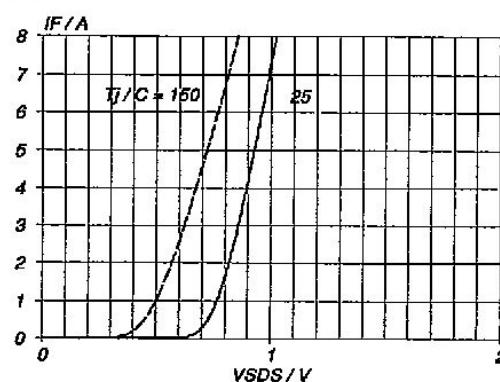


Fig.14. Typical reverse diode current.
 $I_F = f(V_{DS})$; conditions: $V_{GS} = 0 \text{ V}$; parameter T_j